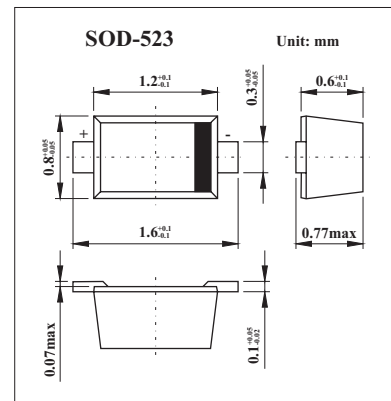


1PS79SB30

■ Features

- Very Low forward voltage
- Very Low reverse current
- Guard ring protected
- Ultra small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V _R			40	V
continuous forward current	I _F			200	mA
repetitive peak forward current	I _{FSM}	t _p ≤ 1 s; δ ≤ 0.5		300	mA
non-repetitive peak forward current	I _{FSM}	t = 8.3 ms half sinewave; JEDEC method		1	A
storage temperature	T _{stg}		-65	+150	°C
junction temperature	T _j			150	°C
operating ambient temperature	T _{amb}		-65	+150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Typ	Max	Unit
forward voltage	V _F	I _F = 0.1 mA	190	220	mV
		I _F = 1 mA	250	290	
		I _F = 10 mA	320	360	
		I _F = 100 mA	440	500	
		I _F = 200 mA	520	600	
capacitance reverse current	I _R	V _R = 25 V, note 1;		0.5	μ A
diodes capacitance	C _d	V _R = 1 V, f = 1 MHz;		20	pF
thermal resistance from junction to ambient	R _{th j-a}			450	K/W

Note

1. Pulse test: pulse width = 300 μ s, δ = 0.02.

■ Marking

Marking	G1
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